IRF6218PBF-VB Datasheet
P-Channel 150 V (D-S) MOSFET

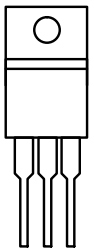
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 150	0.100 at V_{GS} = - 10 V	- 20	13.7
	0.120 at V_{GS} = - 4.5 V	- 18	

FEATURES
- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

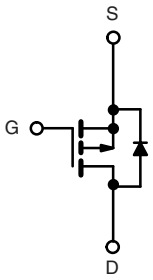
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS
- Power Switch
- DC/DC Converters

TO-220AB



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 20	A
	T_C = 70 °C		- 16	
Pulsed Drain Current		I_{DM}	- 60	
Avalanche Current		I_{AS}	- 18	
Single Avalanche Energy[a]	L = 0.1 mH	E_{AS}	17.2	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	37.1[b]	W
	T_A = 25 °C[c]		2.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	3.9	

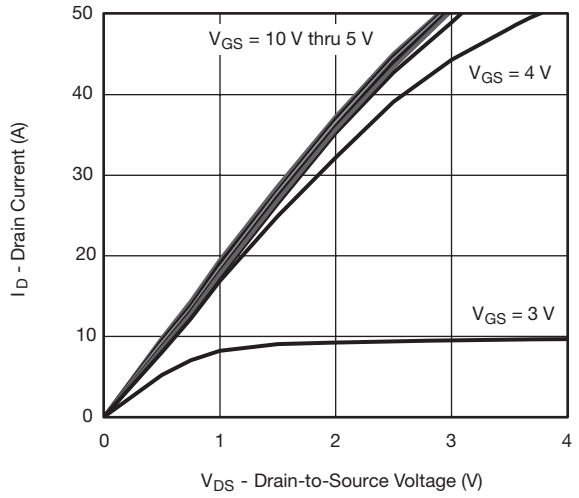
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = - 250 µA	- 150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 100 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 150 V, V_{GS} = 0 V, T_J = 125 °C			- 50	
		V_{DS} = - 150 V, V_{GS} = 0 V, T_J = 150 °C			- 250	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 10 V, V_{GS} = - 10 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 5.0A		0.100		Ω
		V_{GS} = - 4.5 V, I_D = - 4.0 A		0.120		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 5.0 A		12		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 75 V, f = 1 MHz		1055		pF
Output Capacitance	C_{oss}			65		
Reverse Transfer Capacitance	C_{rss}			41		
Total Gate Charge[c]	Q_g	V_{DS} = - 75V, V_{GS} = - 10 V, I_D = - 5.0 A		23.2	34.8	nC
		V_{DS} = - 75 V, V_{GS} = - 4.5 V, I_D = - 5.0 A		13.7	19.6	
Gate-Source Charge[c]	Q_{gs}			4.5		
Gate-Drain Charge[c]	Q_{gd}			5.8		
Gate Resistance	R_g	f = 1 MHz	1.2	5.7	11.5	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 75 V, R_L = 17.2 Ω $I_D \cong$ - 2.9 A, V_{GEN} = - 10 V, R_g = 1 Ω		7	14	ns
Rise Time[c]	t_r			12	18	
Turn-Off Delay Time[c]	$t_{d(off)}$			33	50	
Fall Time[c]	t_f			9	18	
Drain-Source Body Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				- 8.8	A
Pulsed Current	I_{SM}				- 15	
Forward Voltage[a]	V_{SD}	I_F = - 2.9 A, V_{GS} = 0 V		- 0.8	- 1.5	V
Reverse Recovery Time	t_{rr}	I_F = - 2.9 A, dI/dt = 100 A/µs		50	75	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			- 4	- 6	A
Reverse Recovery Charge	Q_{rr}			98	147	nC

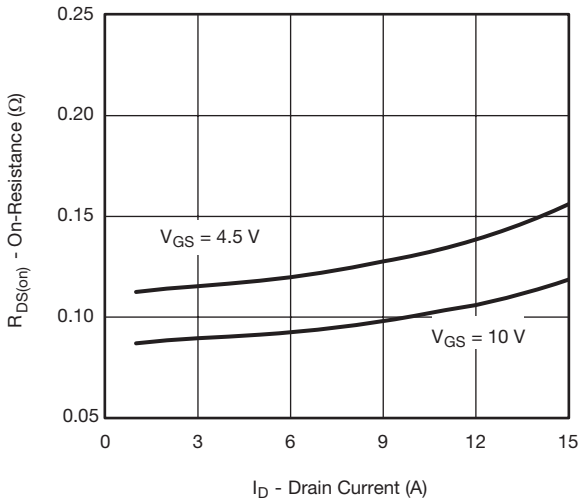
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

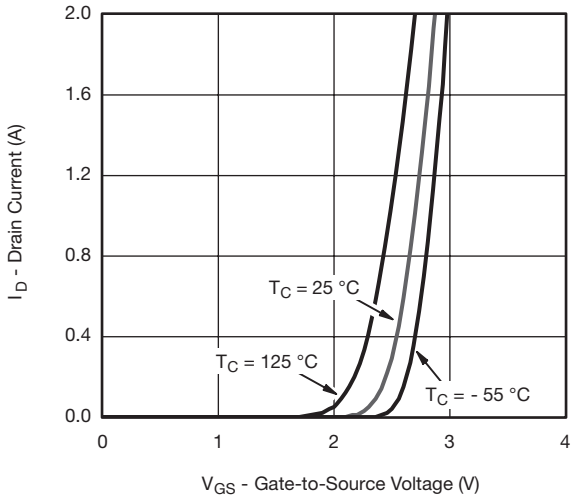
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



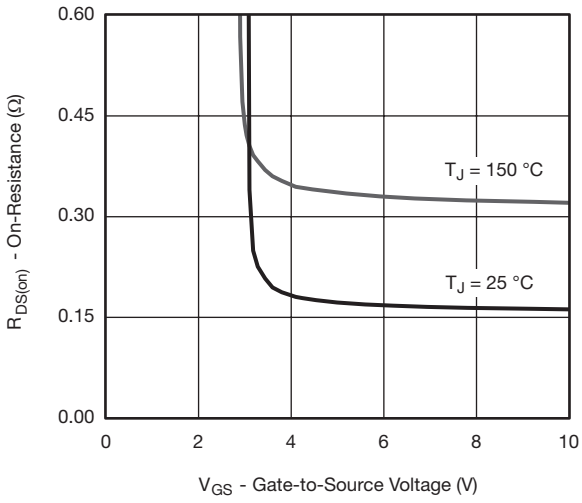
Output Characteristics



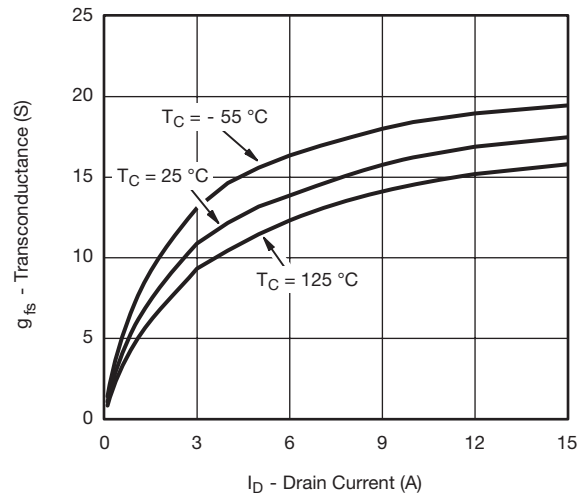
On-Resistance vs. Drain Current



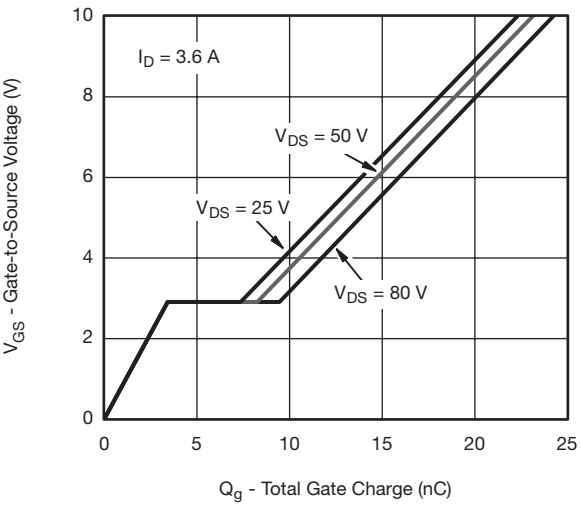
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

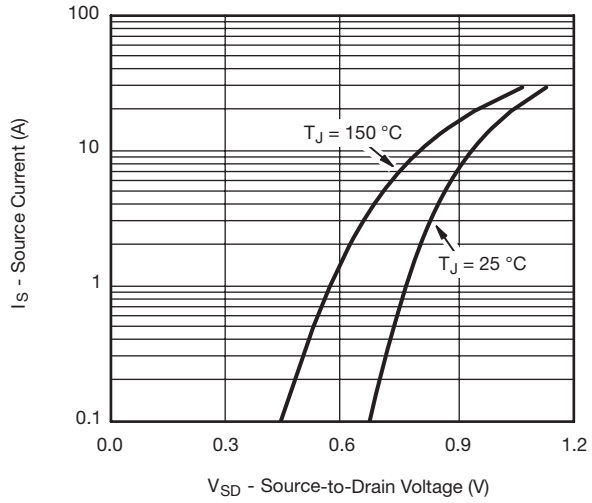


Transconductance

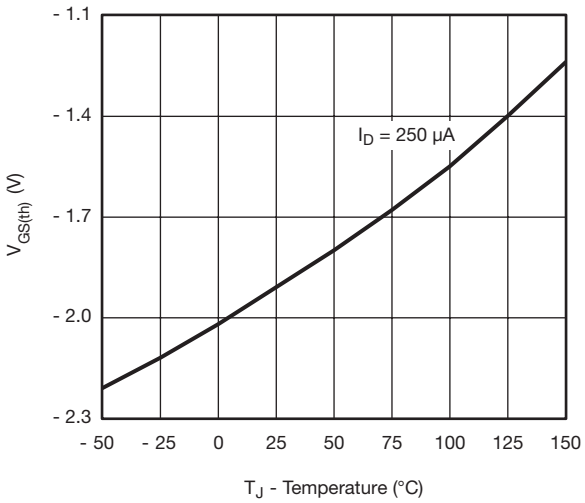


Gate Charge

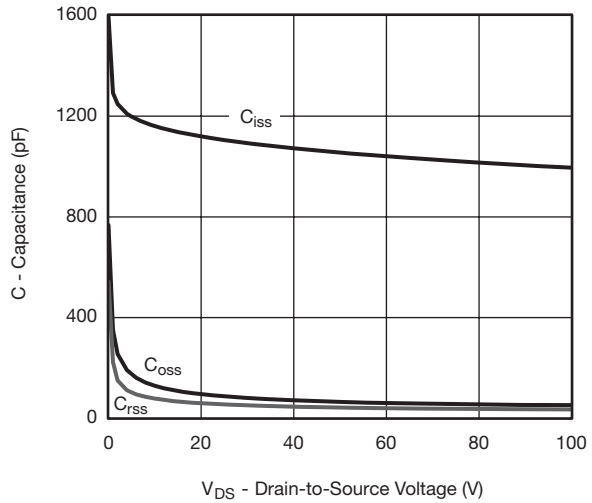
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



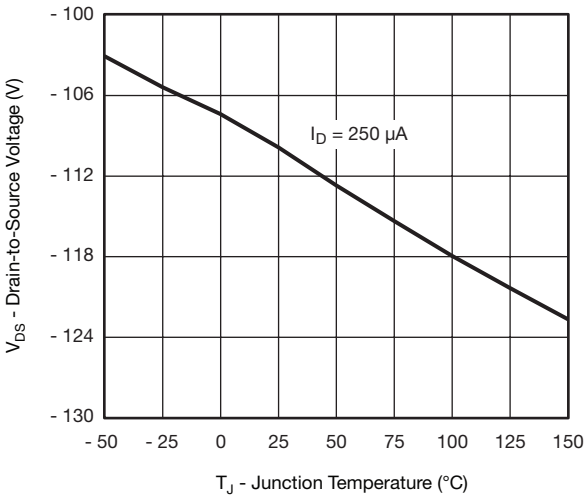
Source-Drain Diode Forward Voltage



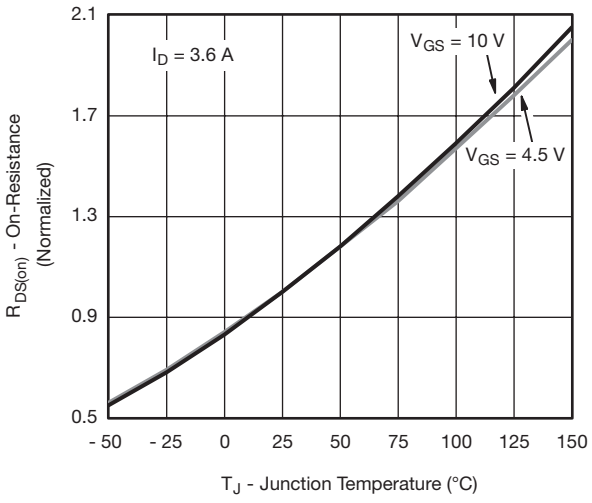
Threshold Voltage



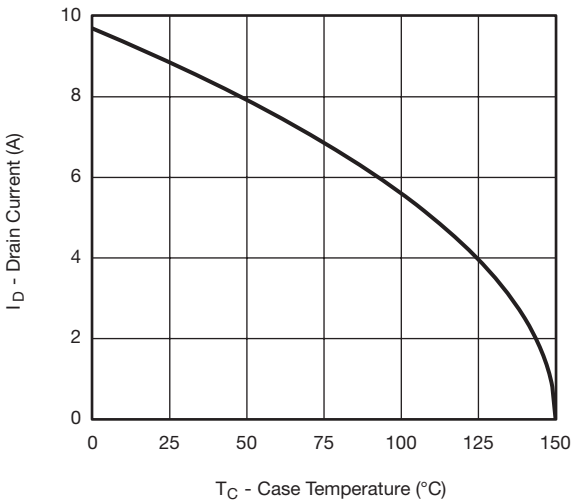
Capacitance



Drain Source Breakdown vs. Junction Temperature

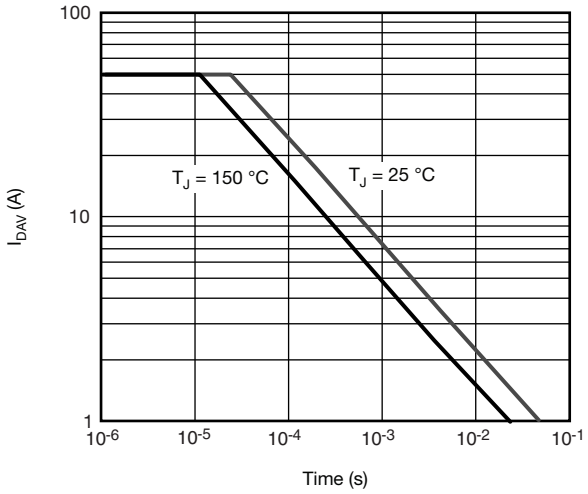


On-Resistance vs. Junction Temperature

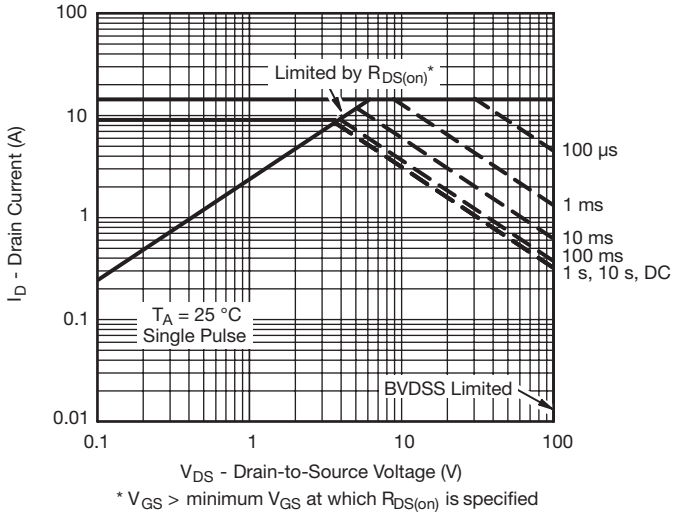


Current Derating

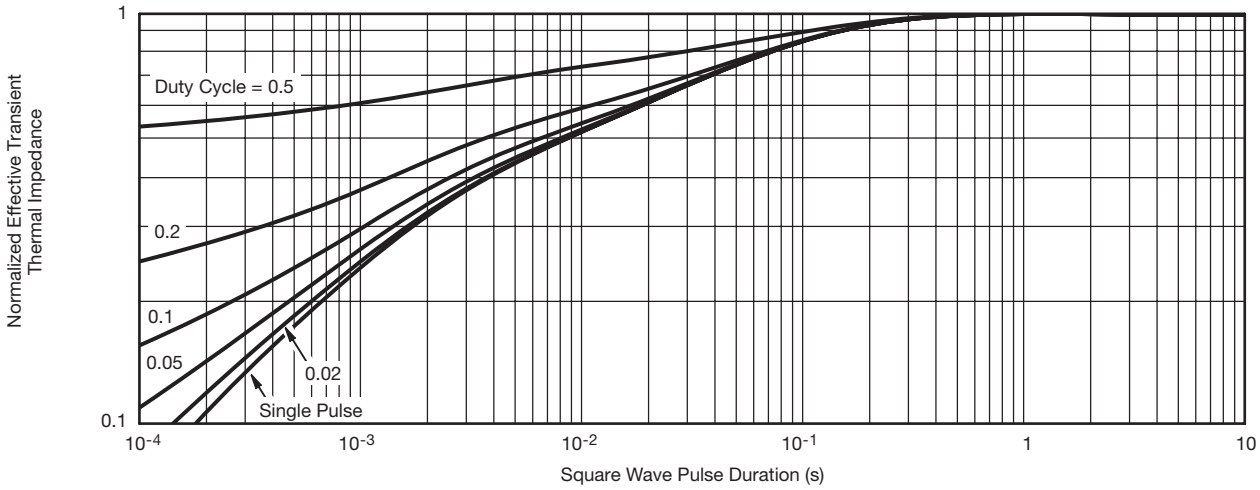
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time

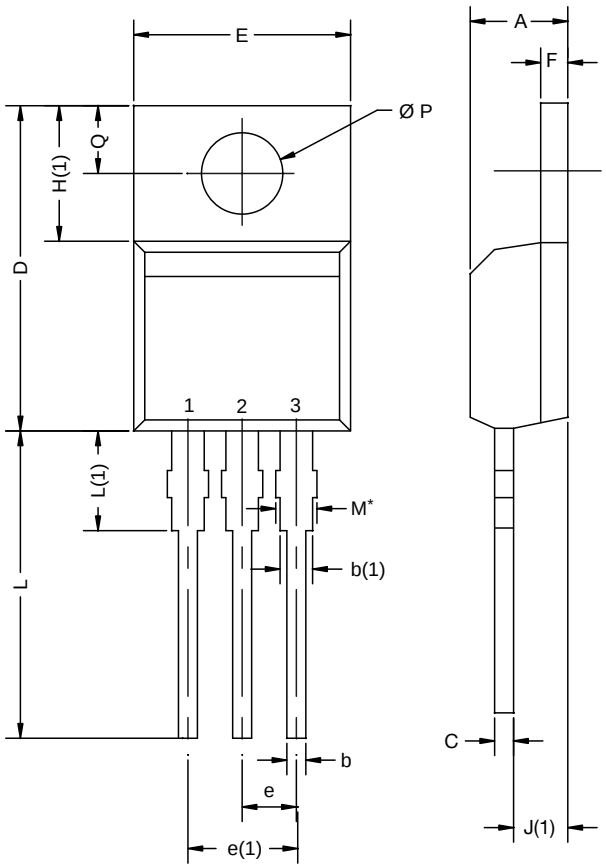


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12 DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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